

DERWENT-ACC-NO: 2001-519673
DERWENT-WEEK: 200157
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TITLE: Decreasing removing rate of polishing for low dielectric constant material comprises directly integrating low dielectric constant material into copper damascene process

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
TW 420844 A	February 1, 2001	N/A	020	H01L 021/304

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO	APPL-DATE
TW 420844A	N/A	1999TW-0110309	June 21, 1999

INT-CL (IPC): H01L021/304

ABSTRACTED-PUB-NO: TW 420844A

BASIC-ABSTRACT: NOVELTY - Decreasing the removing rate of polishing for low

dielectric constant material comprises depositing a low dielectric constant material on a semiconductor substrate to form a dielectric layer, and performing an NH3 plasma, N2 plasma or Ar plasma process to increase the density degree of the dielectric layer, thereby decreasing the removing rate of polishing.

ADVANTAGE - The selectivity of chemical mechanical polishing process is increased, so as to assist the integration of the low dielectric constant material and copper damascene process.

CHOSEN-DRAWING: Dwg.1/2

TITLE-TERMS:

DECREASE REMOVE RATE POLISH LOW DIELECTRIC CONSTANT
MATERIAL COMPRISE INTEGRATE
LOW DIELECTRIC CONSTANT MATERIAL COPPER PROCESS

DERWENT-CLASS: L03 U11

CPI-CODES: L04-C26;

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SECONDARY-ACC-NO:

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